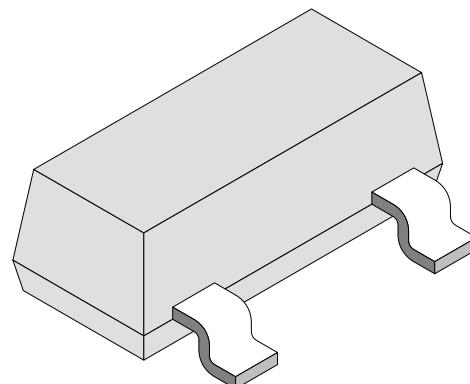


# Surface Mount Switching Diode

## Features

- Silicon planar epitaxial high speed diode
- For switching and general purpose applications



94 8550

## Absolute Maximum Ratings

 $T_j = 25^\circ\text{C}$ 

| Parameter  | Test Conditions                               | Type  | Symbol               | Value      | Unit |
|--|---|-------|----------------------|------------|------|
| Working peak reverse voltage<br>=DC Blocking voltage |   | BAS19 | $V_{RWM}$<br>= $V_R$ | 100        | V    |
|  |   | BAS20 |                      | 150        | V    |
|  |   | BAS21 |                      | 200        | V    |
| Repetitive peak reverse voltage                      |   | BAS19 | $V_{RRM}$            | 120        | V    |
|  |   | BAS20 | $V_{RRM}$            | 200        | V    |
|  |   | BAS21 | $V_{RRM}$            | 250        | V    |
| Peak forward surge current                           | $t=1\mu\text{s}$                              |       | $I_{FSM}$            | 2.5        | A    |
|  | $t=1\text{s}$                                 |       | $I_{FSM}$            | 0.5        | A    |
| Repetitive peak forward current                      |   |       | $I_{FRM}$            | 625        | mA   |
| Average forward current                              | $t_p < 0.3\text{ms}$                          |       | $I_{FAV}$            | 200        | mA   |
| Forward current                                      | $T_{Case}=T_L$ (8mm from Case)<br>= $T_{amb}$ |       | $I_F$                | 400        | mA   |
| Power dissipation                                    | $T_{Case}=T_L$ (8mm from Case)<br>= $T_{amb}$ |       | $P_{tot}$            | 250        | mW   |
| Junction and storage temperature range               |   |       | $T_j=T_{stg}$        | -55...+150 | °C   |

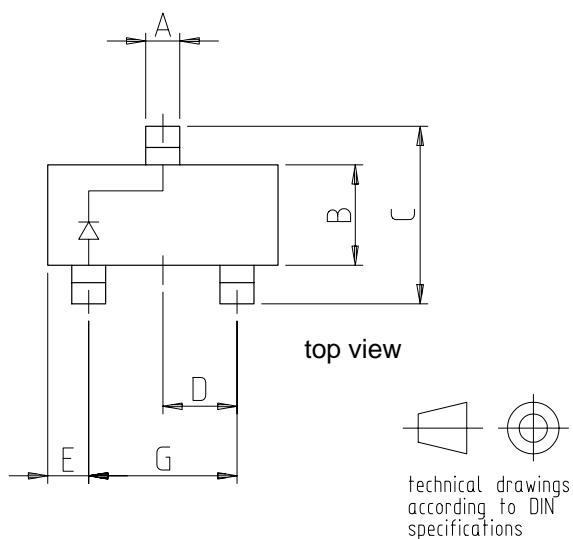
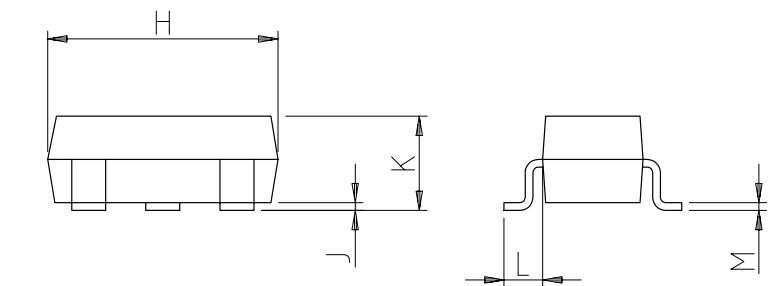
## Maximum Thermal Resistance

 $T_j = 25^\circ\text{C}$ 

| Parameter        | Test Conditions | Symbol     | Value | Unit |
|------------------|-----------------|------------|-------|------|
| Junction ambient |                 | $R_{thJA}$ | 500   | K/W  |

**Electrical Characteristics** $T_j = 25^\circ\text{C}$ 

| Parameter                  | Test Conditions  | Type  | Symbol      | Min | Typ | Max  | Unit          |
|----------------------------|--|-------|-------------|-----|-----|------|---------------|
| Forward voltage            | $I_F=100\text{mA}$   |       | $V_F$       |     |     | 1.0  | V             |
|                            | $I_F=200\text{mA}$   |       | $V_F$       |     |     | 1.25 | V             |
| Reverse current            | $V_R=V_{R\text{max}}$  |       | $I_R$       |     |     | 100  | nA            |
|                            | $V_R=V_{R\text{max}}, T_j= 150^\circ\text{C}$  |       | $I_R$       |     |     | 100  | $\mu\text{A}$ |
| Reverse breakdown voltage  | $I_R=100\mu\text{A}, t_p<0.3\text{ms}$   | BAS19 | $V_{(BR)R}$ | 120 |     |      | V             |
|                            | $I_R=100\mu\text{A}$   | BAS20 | $V_{(BR)R}$ | 200 |     |      | V             |
|                            | $I_R=100\mu\text{A}, V_R<275\text{V}$  | BAS21 | $V_{(BR)R}$ | 250 |     |      | V             |
| Reverse recovery time      | $I_F=I_R=10\text{mA}, R_L=100\Omega, V_R=6\text{V to } I_R=1\text{mA. } R_L=100\Omega$ |       | $t_{rr}$    |     |     | 50   | ns            |
| Diode capacitance          | $V_R=0, f= 1\text{MHz}$  |       | $C_D$       |     |     | 5    | pF            |
| Dynamic forward resistance | $I_F=10\text{mA}$  |       | $r_f$       |     |     | 5    | $\Omega$      |

**Dimensions in mm**


| SOT-23 |       |       |
|--------|-------|-------|
| Dim    | Min   | Max   |
| A      | 0.37  | 0.50  |
| B      | 1.19  | 1.40  |
| C      | 2.10  | 2.50  |
| D      | 0.89  | 1.05  |
| E      | 0.45  | 0.61  |
| G      | 1.78  | 2.05  |
| H      | 2.79  | 3.05  |
| J      | 0.013 | 0.15  |
| K      | 0.89  | 1.10  |
| L      | 0.45  | 0.61  |
| M      | 0.076 | 0.130 |

All Dimensions in mm

Case: SOT-23, plastic

Terminals: Solderable per MIL-STD-202, Method 208

Approx. weight: 0.008 grams

Marking: BAS19 K80,

BAS20 K81,

BAS21 K82

## **Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems  
with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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